

FIG. 1

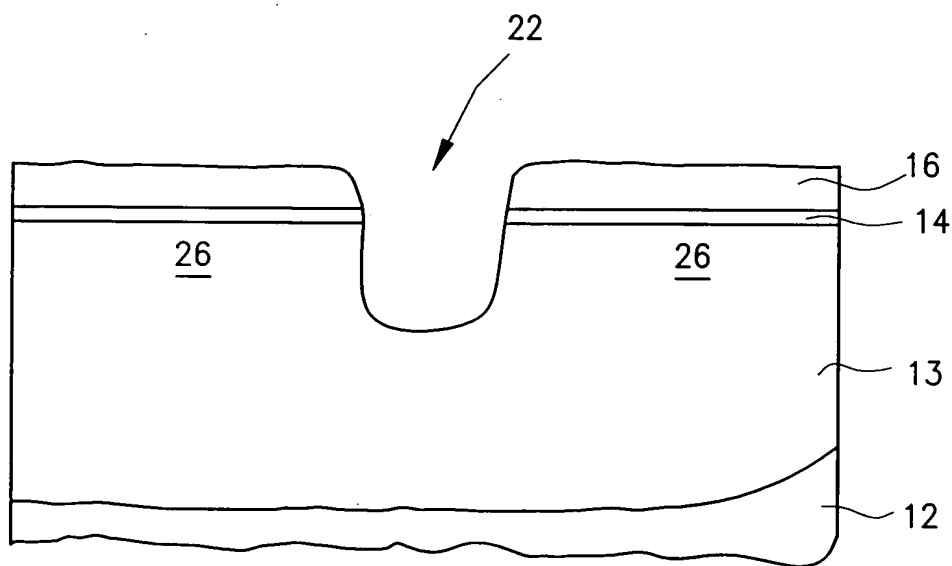
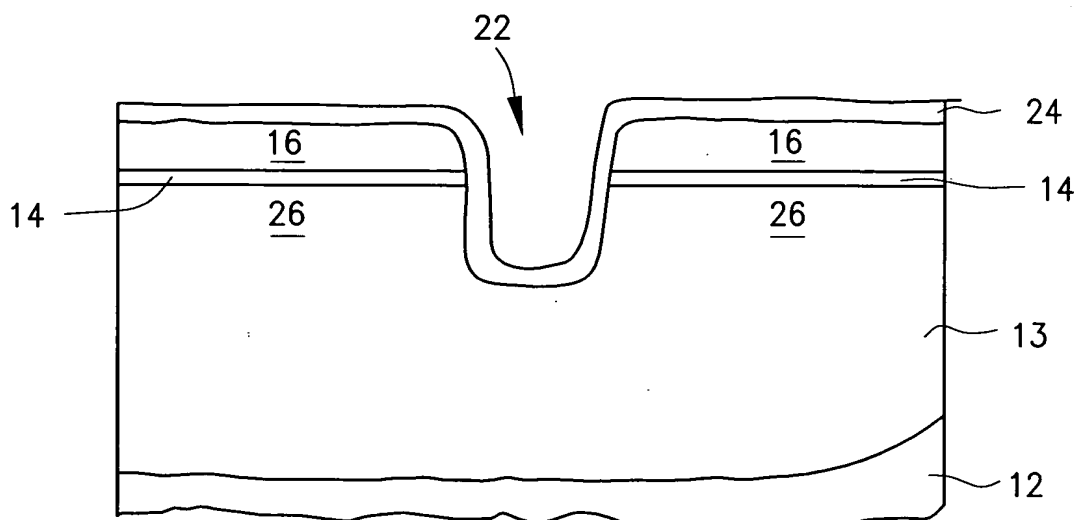


FIG. 2



A cross-sectional diagram of a semiconductor device. At the top, seven downward-pointing arrows are labeled "ION IMPLANT". The device structure consists of several layers: a top layer labeled "30" with diagonal hatching; a thin layer labeled "16"; a layer labeled "26"; and a bottom layer labeled "12". A central feature is a trench or well labeled "22" with a bottom labeled "28". On the right side, there is a vertical stack of layers labeled "24", "16", "14", and "13". Two arrows point to the bottom of the trench "22": one is labeled "SHALLOW IMPLANT PROFILE" and the other is labeled "DEEP IMPLANT PROFILE".

FIG. 4

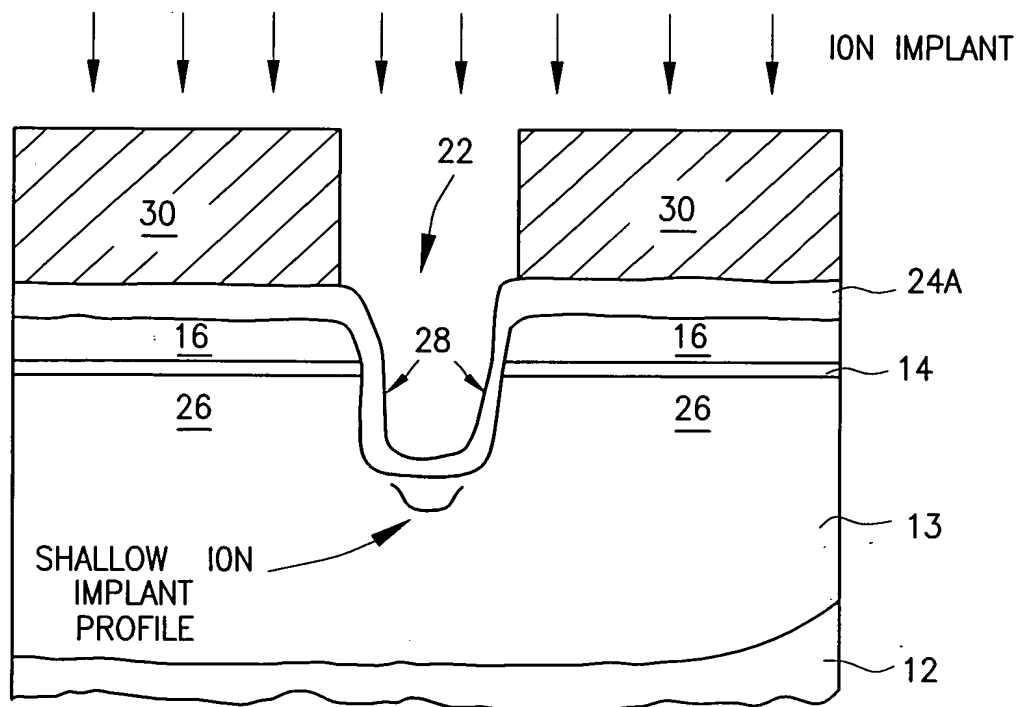


FIG. 5

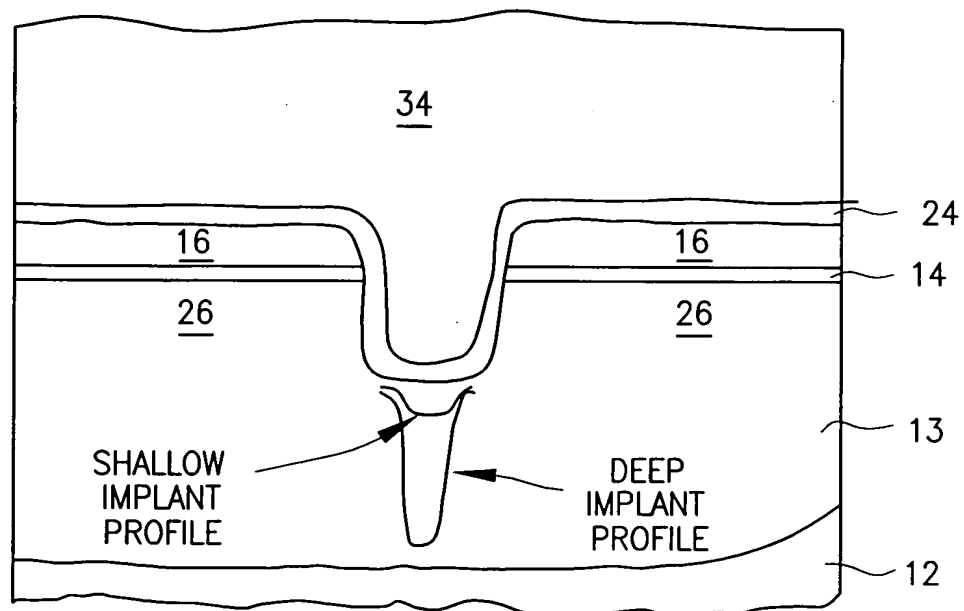


FIG. 6

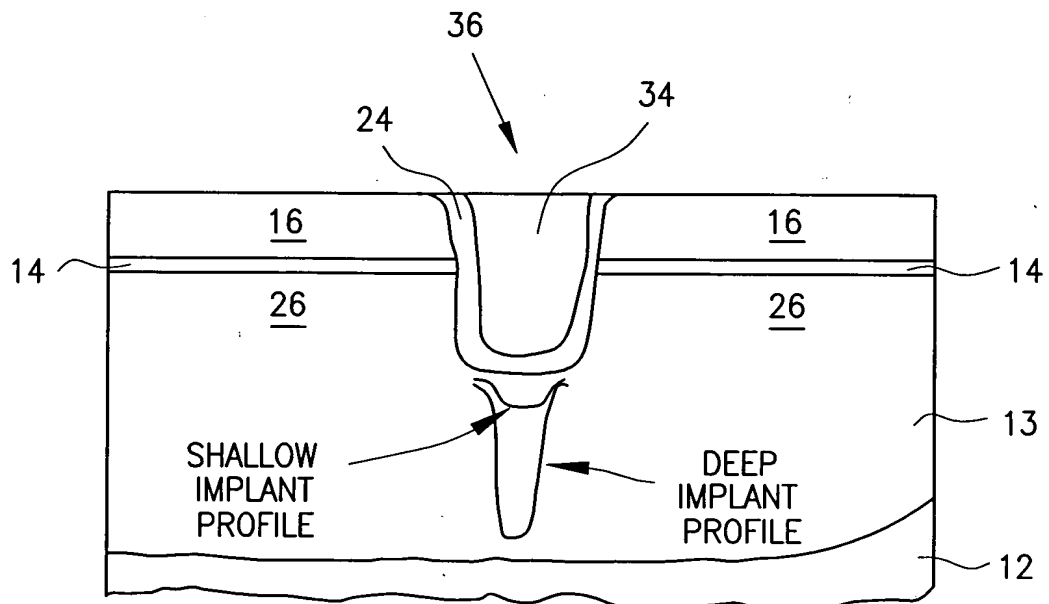


FIG. 7

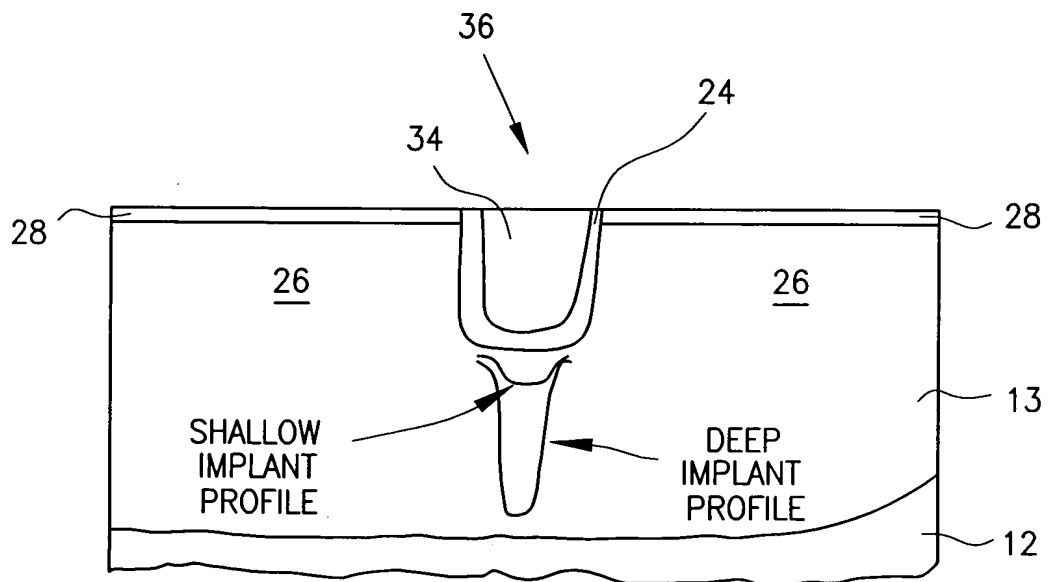
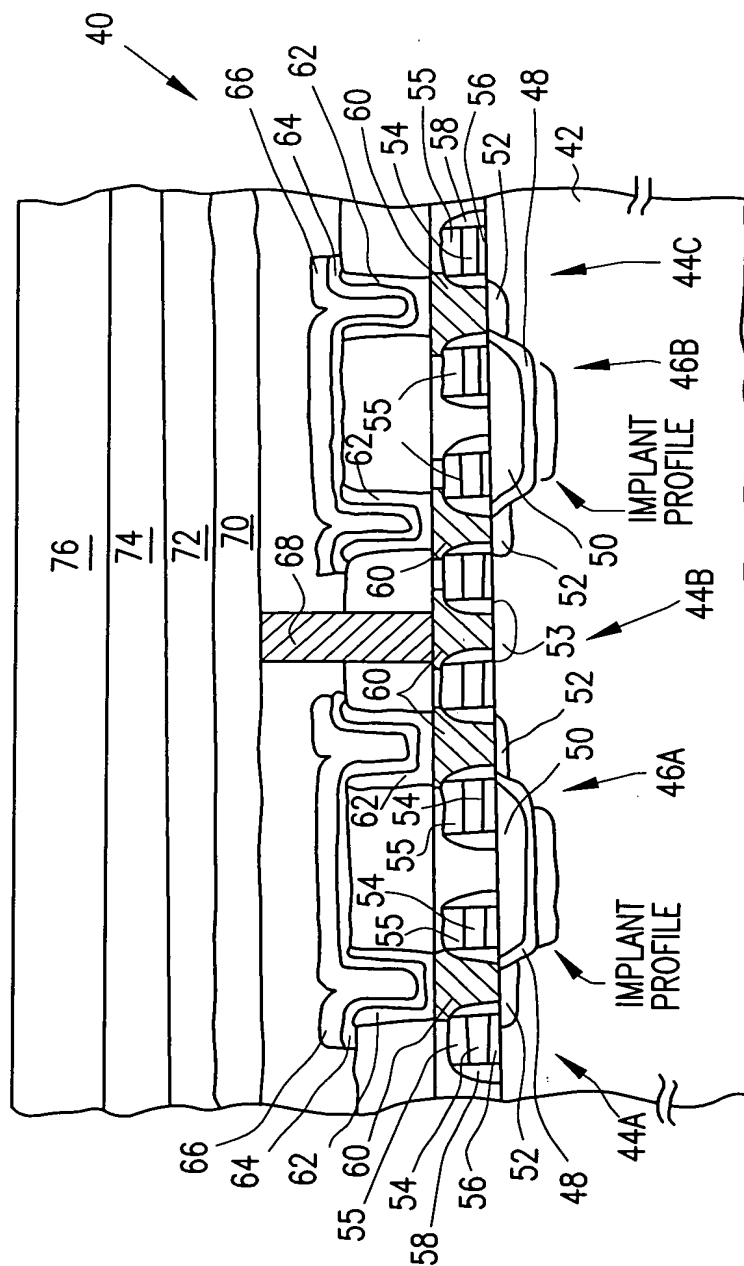


FIG. 8

FIG. 9



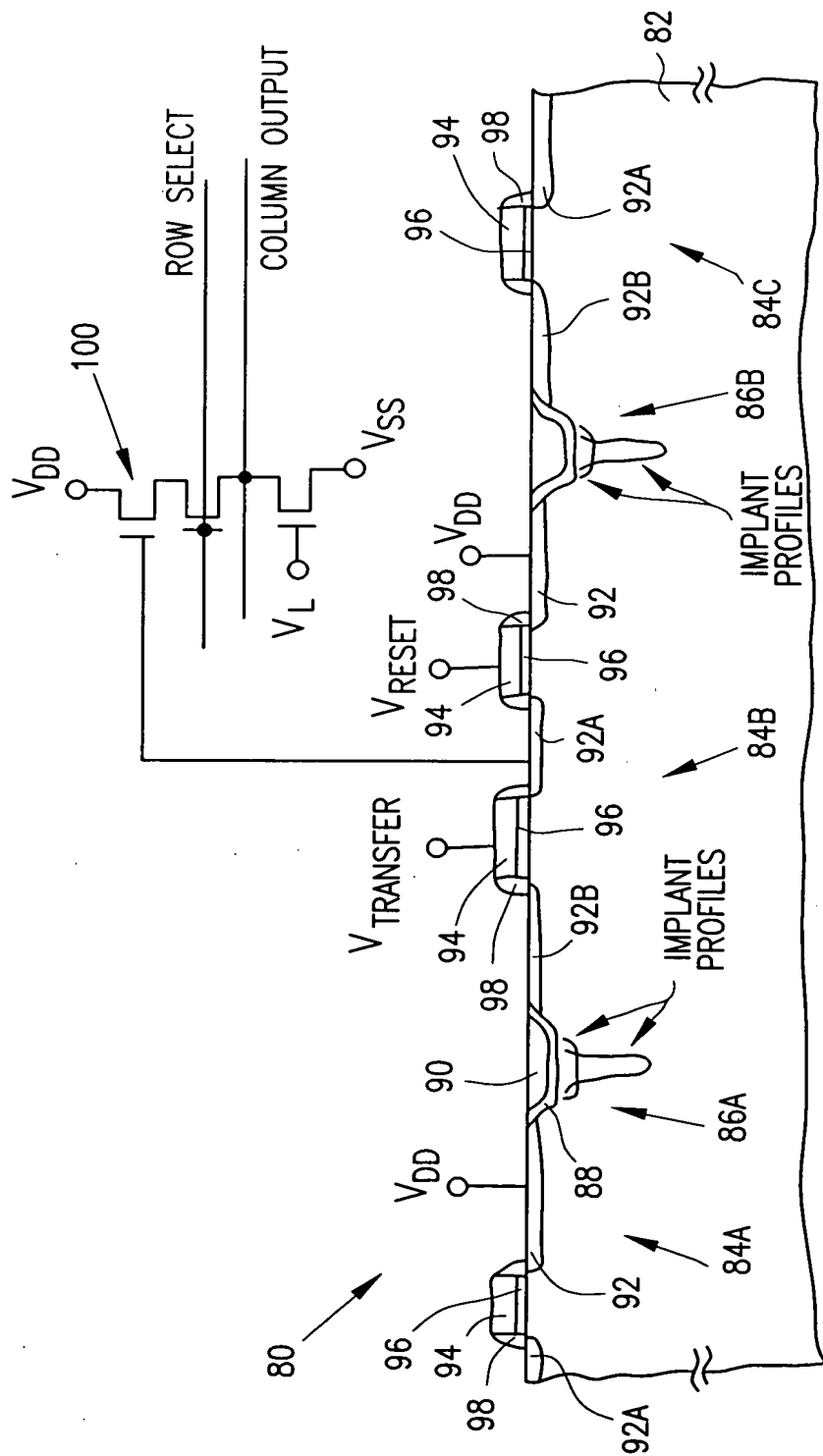


FIG. 10